

N0412N

N-channel MOSFET

40 V, 100 A, 3.7 mΩ

R07DS0554EJ0200

Rev.2.00

2020.6.10

Features

- Low on-state resistance : $R_{DS(on)} = 3.7 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 10 \text{ V}$, $I_D = 50 \text{ A}$)
- Low C_{iss} : $C_{iss} = 5550 \text{ pF TYP.}$ ($V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$)
- High current : $I_{D(DC)} = \pm 100 \text{ A}$
- RoHS Compliant
- Quality Grade : Standard
- Applications : For high current switching

Ordering Information

Part No.	Package	Packing
N0412N-S19-AY	TO-220AB, Pb-free ^{Note1}	50 pcs / Magazine (Tube)

Note: 1. Pb-free means that this product does not contain lead in the external electrode.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	40	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 100	A
Drain Current (pulse) ^{Note2}	$I_{D(pulse)}$	± 400	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	119	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	1.5	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note3}	I_{AS}	55	A
Single Avalanche Energy ^{Note3}	E_{AS}	300	mJ

Note: Continuous heavy condition (e.g. high temperature/voltage/current or high variation of temperature) may affect a reliability even if it is within the absolute maximum ratings. Please consider derating condition for appropriate reliability in reference Renesas Semiconductor Reliability Handbook (Recommendation for Handling and Usage of Semiconductor Devices) and individual reliability data.

Notes: 2. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

3. Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{DD} = 25 \text{ V}$, $V_{GS} = 20 \rightarrow 0 \text{ V}$, $L = 100 \mu\text{H}$

Thermal Resistance

Item	Symbol	Max. Value ^{Note4}	Unit
Channel to Case Thermal Resistance	$R_{th(ch-C)}$	1.05	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	83.3	$^\circ\text{C/W}$

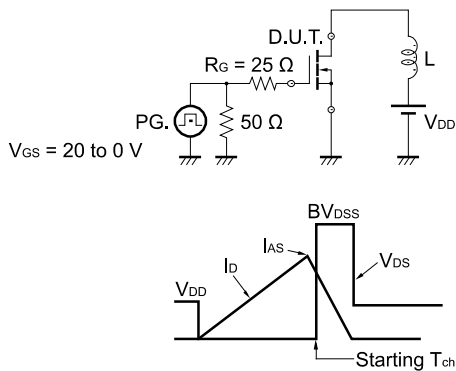
Notes: 4. This data is the designed target maximum value on Renesas's measurement condition. (Not tested)

Electrical Characteristics (T_A = 25°C)

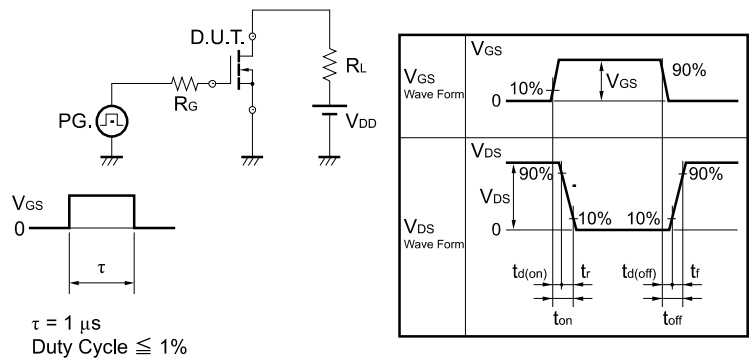
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 40 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±100	nA	V _{GS} = ±20 V, V _{DS} = 0 V
Gate to Source Cut-off Voltage	V _{GS(off)}	2.0		4.0	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance ^{Note5}	y _{fs}	26			S	V _{DS} = 10 V, I _D = 50 A
Drain to Source On-state Resistance ^{Note5}	R _{DS(on)}		2.7	3.7	mΩ	V _{GS} = 10 V, I _D = 50 A
Input Capacitance	C _{iss}		5550		pF	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz
Output Capacitance	C _{oss}		580		pF	
Reverse Transfer Capacitance	C _{rss}		320		pF	
Turn-on Delay Time	t _{d(on)}		29.0		ns	V _{DD} = 20 V, I _D = 50 A, V _{GS} = 10 V, R _G = 0 Ω
Rise Time	t _r		15.0		ns	
Turn-off Delay Time	t _{d(off)}		64.0		ns	
Fall Time	t _f		13.0		ns	
Total Gate Charge	Q _G		100		nC	V _{DD} = 32 V, V _{GS} = 10 V, I _D = 100 A
Gate to Source Charge	Q _{GS}		26		nC	
Gate to Drain Charge	Q _{GD}		32		nC	
Body Diode Forward Voltage ^{Note5}	V _{F(S-D)}			1.5	V	I _F = 100 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		40		ns	I _F = 50 A, V _{GS} = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q _{rr}		44		nC	

Notes: 5. Pulsed test

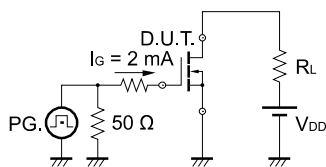
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

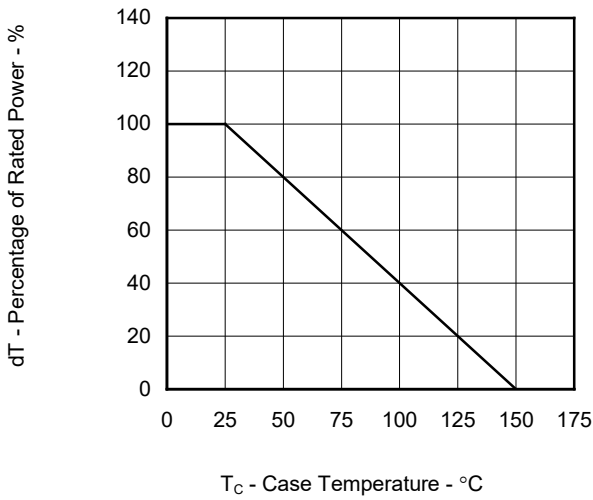


TEST CIRCUIT 3 GATE CHARGE

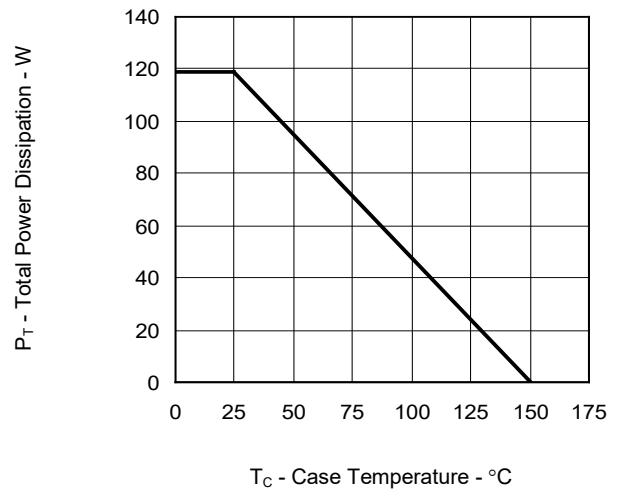


Typical Characteristics Note6

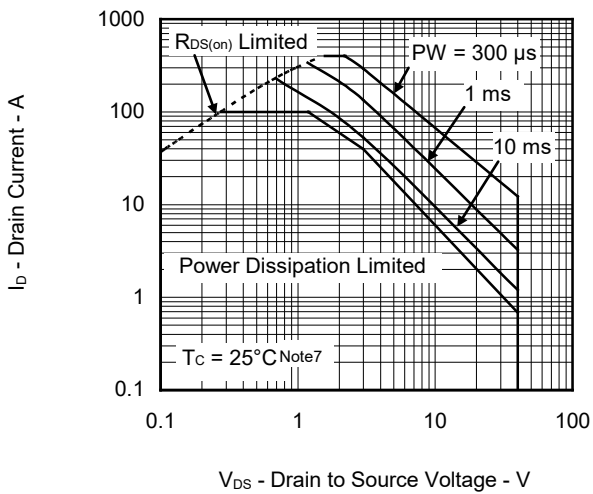
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



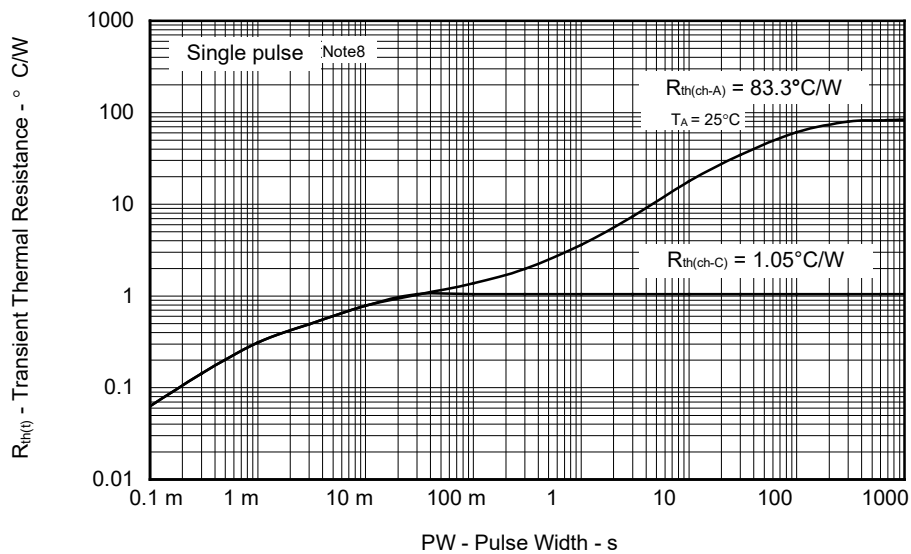
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



FORWARD BIAS SAFE OPERATING AREA

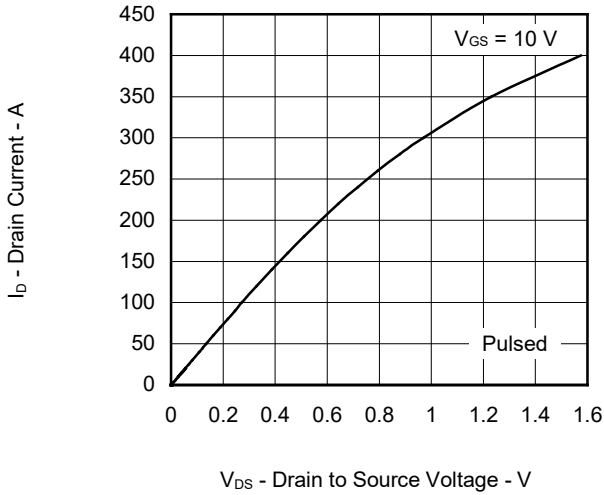


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

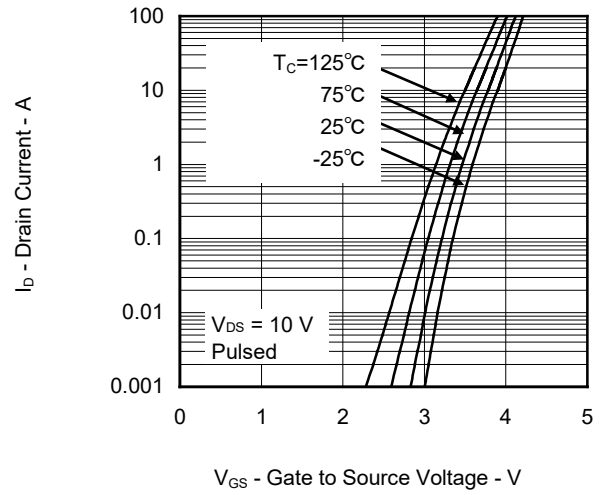


- Notes: 6. Designed target value on Renesas measurement condition. ($T_C = 25^\circ\text{C}$, unless otherwise specified)
 7. This data is the designed value on Renesas's measurement condition. Renesas recommends that operating conditions are designed according to a document "Power MOSFET/IGBT Attention of Handling Semiconductor Devices (R07ZZ0010)".
 8. This data is the designed target maximum value on Renesas's measurement condition.

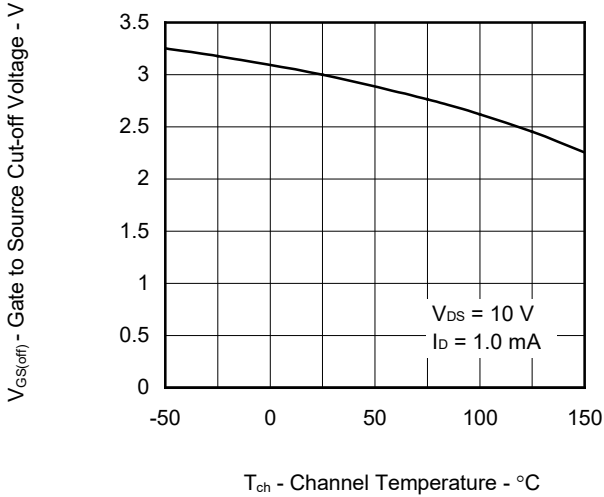
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



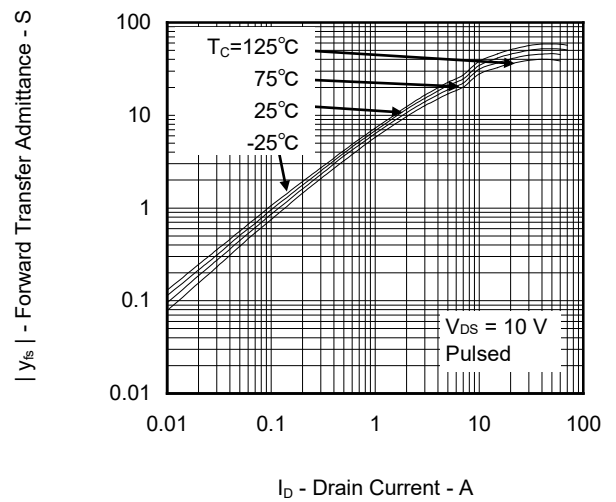
FORWARD TRANSFER CHARACTERISTICS



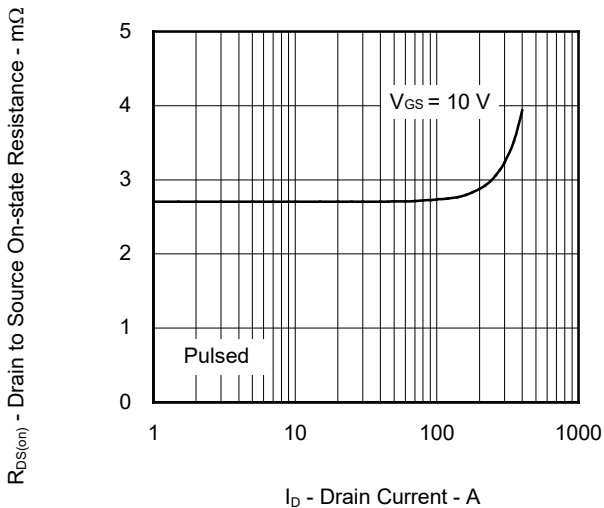
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



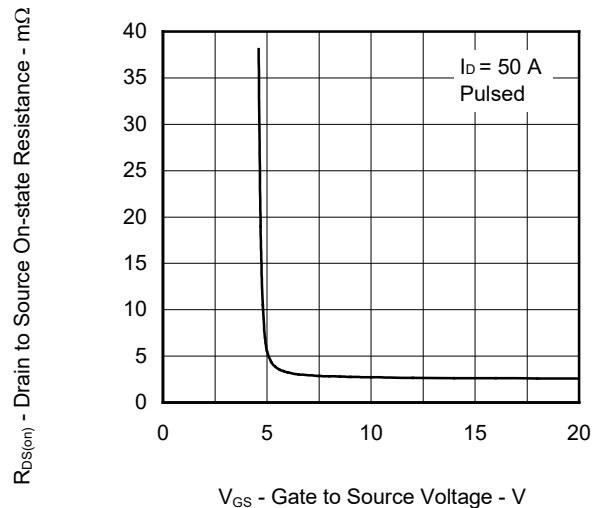
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



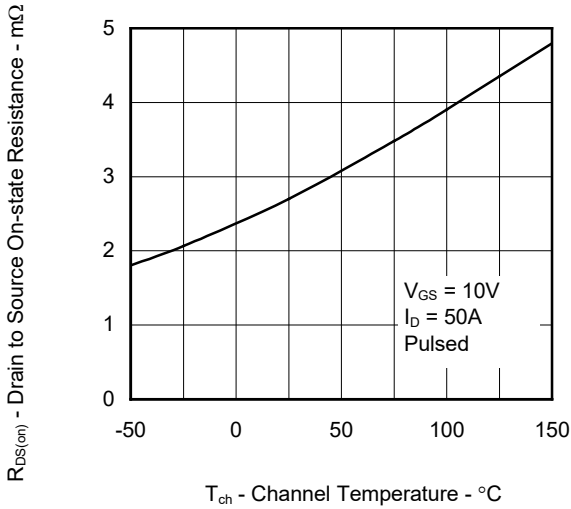
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



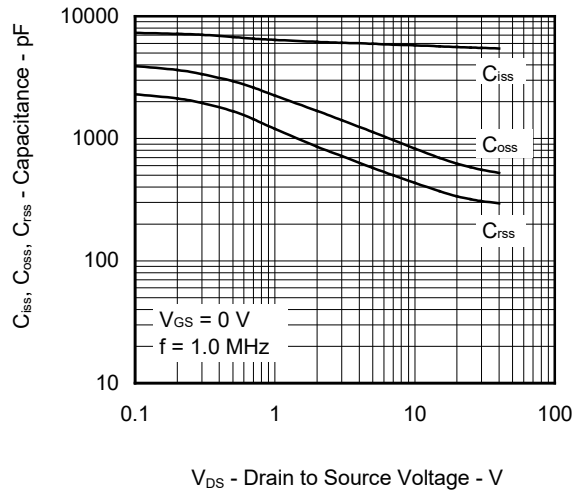
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



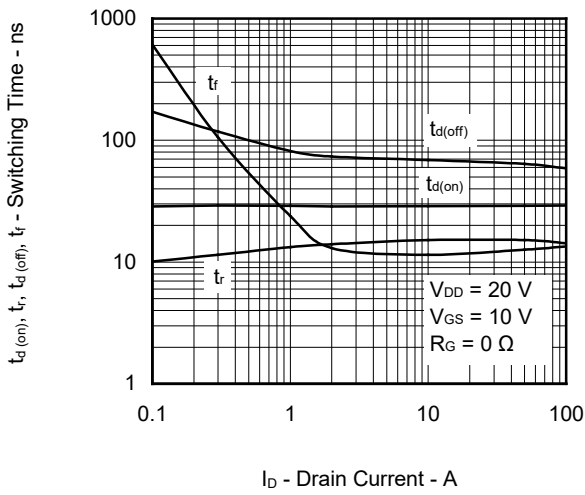
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



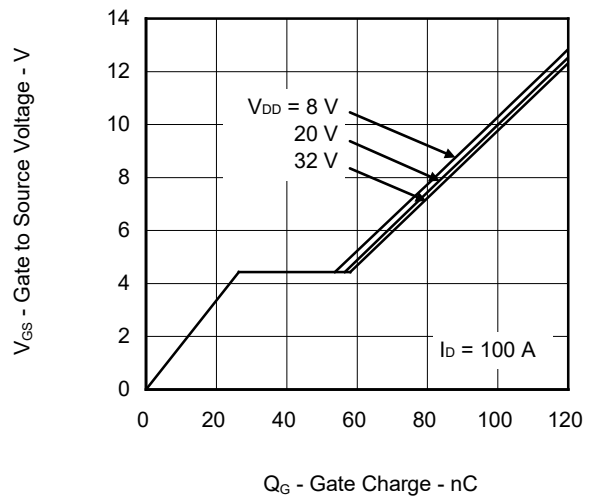
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



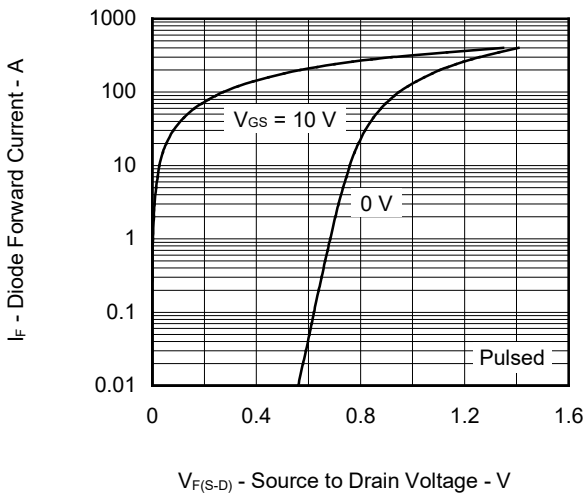
SWITCHING CHARACTERISTICS



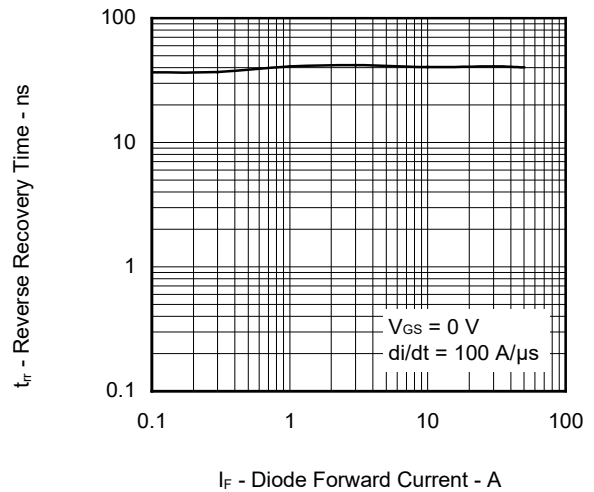
DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



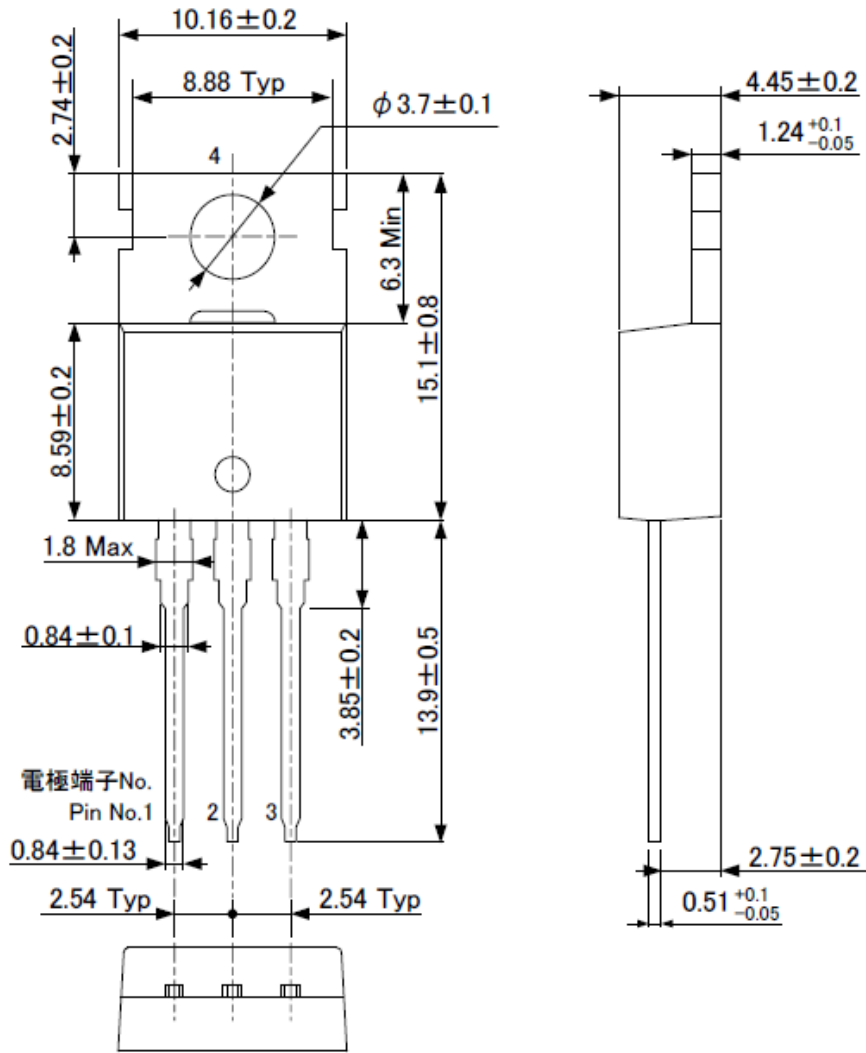
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



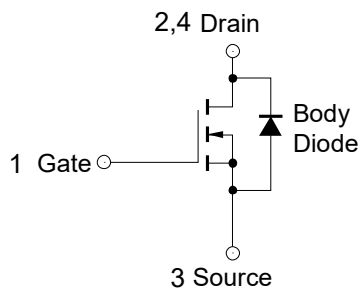
Package Drawing (Unit: mm)

JEDEC Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
TO-220AB	PRSS0004AU-A	TO-220ABB	2.1

Unit: mm



Equivalent Circuit



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Renesas Electronics America Inc. Milpitas Campus
1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.
Tel: +1-408-432-8888, Fax: +1-408-434-5351

Renesas Electronics America Inc. San Jose Campus
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Tel: +1-905-237-2004

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40477 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 101-T01, Floor 1, Building 7, Yard No. 7, 8th Street, Shangdi, Haidian District, Beijing 100085, China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai 200333, China
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852-2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, #06-02 Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit No 3A-1 Level 3A Tower 8 UOA Business Park, No 1 Jalan Pengaturcara U1/51A, Seksyen U1, 40150 Shah Alam, Selangor, Malaysia
Tel: +60-3-5022-1288, Fax: +60-3-5022-1290

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India
Tel: +91-80-67208700

Renesas Electronics Korea Co., Ltd.
17F, KAMICO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5338

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